# **Dual 4-Bit Static Shift Register**

The MC14015B dual 4-bit static shift register is constructed with MOS P-Channel and N-Channel enhancement mode devices in a single monolithic structure. It consists of two identical, independent 4-state serial-input/parallel-output registers. Each register has independent Clock and Reset inputs with a single serial Data input. The register states are type D master-slave flip-flops. Data is shifted from one stage to the next during the positive-going clock transition. Each register can be cleared when a high level is applied on the Reset line. These complementary MOS shift registers find primary use in buffer storage and serial-to-parallel conversion where low power dissipation and/or noise immunity is desired.

#### **Features**

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Logic Edge-Clocked Flip-Flop Design
- Logic State is Retained Indefinitely with Clock Level either High or Low; Information is Transferred to the Output only on the Positive-going Edge of the Clock Pulse
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb–Free and is RoHS Compliant



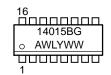
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SOIC-16 D SUFFIX CASE 751B

#### MARKING DIAGRAM



A = Assembly Location

WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Indicator

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

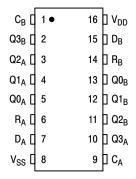
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$ .

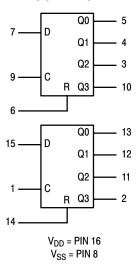
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either VSS or VDD). Unused outputs must be left open.

<sup>1.</sup> Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65°C To 125°C

#### **PIN ASSIGNMENT**



#### **BLOCK DIAGRAM**



**TRUTH TABLE** 

С	D	R	Q0	Q <sub>n</sub>
	0	0	0	$Q_{n-1}$
	1	0	1	$Q_{n-1}$
~	Х	0	No Change	No Change
Х	Х	1	0	0

X = Don't Care

 $Q_n = Q0$ , Q1, Q2, or Q3, as applicable.

 $Q_{n-1}$  = Output of prior stage.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14015BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14015BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14015BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				-55	5°C		25°C		125	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05		0 0 0	0.05 0.05 0.05		0.05 0.05 0.05	Vdc
$V_{in} = 0$ or $V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95		4.95 9.95 14.95	5.0 10 15		4.95 9.95 14.95		Vdc
Input Voltage ( $V_O = 4.5 \text{ or } .05 \text{ Vdc}$ ) ( $V_O = 9.0 \text{ or } 1.0 \text{ Vdc}$ ) ( $V_O = 13.5 \text{ or } 1.5 \text{ Vdc}$ )	"0" Level	V <sub>IL</sub>	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current $ (V_{OH} = 2.5 \text{ Vdc}) $ $ (V_{OH} = 4.6 \text{ Vdc}) $ $ (V_{OH} = 9.5 \text{ Vdc}) $ $ (V_{OH} = 13.5 \text{ Vdc}) $	Source	ГОН	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2		-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	1 1 1 1	-1.7 -0.36 -0.9 -2.4		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8		0.36 0.9 2.4	- - -	mAdc
Input Current		I <sub>in</sub>	15	-	±0.1	-	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdc
Total Supply Current (Notes 3 & 4) (Dynamic plus Quiescent, Per Package) (C <sub>L</sub> = 50 pF on all outputs, all buffers switching)		Ι <sub>Τ</sub>	5.0 10 15			$I_T = (2$	1.2 μΑ/kHz)f 2.4 μΑ/kHz)f 3.6 μΑ/kHz)f	+ I <sub>DD</sub>			μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

3. The formulas given are for the typical characteristics only at 25°C.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.002.

<sup>4.</sup> To calculate total supply current at loads other than 50 pF:

# SWITCHING CHARACTERISTICS (Note 5) (C $_L$ = 50 pF, $T_A$ = $25^{\circ}C)$

Characteristic	Symbol	V <sub>DD</sub>	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time $t_{TLH}, t_{THL} = (1.5 \text{ ns/pF}) \text{ C}_{L} + 25 \text{ ns}$ $t_{TLH}, t_{THL} = (0.75 \text{ ns/pF}) \text{ C}_{L} + 12.5 \text{ ns}$ $t_{TLH}, t_{THL} = (0.55 \text{ ns/pF}) \text{ C}_{L} + 9.5 \text{ ns}$	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time Clock, Data to Q $t_{PLH}, t_{PHL} = (1.7 \text{ ns/pF}) \text{ C}_L + 225 \text{ ns} \\ t_{PLH}, t_{PHL} = (0.66 \text{ ns/pF}) \text{ C}_L + 92 \text{ ns} \\ t_{PLH}, t_{PHL} = (0.5 \text{ ns/pF}) \text{ C}_L + 65 \text{ ns} \\ \text{Reset to Q} \\ t_{PLH}, t_{PHL} = (1.7 \text{ ns/pF}) \text{ C}_L + 375 \text{ ns} \\ t_{PLH}, t_{PHL} = (0.66 \text{ ns/pF}) \text{ C}_L + 147 \text{ ns} \\ t_{PLH}, t_{PHL} = (0.5 \text{ ns/pF}) \text{ C}_L + 95 \text{ ns} \\ \end{cases}$	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0 10 15 5.0 10	- - - -	310 125 90 460 180 120	750 250 170 750 250 170	ns
Clock Pulse Width	t <sub>WH</sub>	5.0 10 15	400 175 135	185 85 55	- - -	ns
Clock Pulse Frequency	f <sub>cl</sub>	5.0 10 15	- - -	2.0 6.0 7.5	1.5 3.0 3.75	MHz
Clock Pulse Rise and Fall Times	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	- - -	- - -	15 5 4	μS
Reset Pulse Width	t <sub>WH</sub>	5.0 10 15	400 160 120	200 80 60	- - -	ns
Setup Time	t <sub>su</sub>	5.0 10 15	350 100 75	100 50 40	- - -	ns

<sup>5.</sup> The formulas given are for typical characteristics only at 25°C.
6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

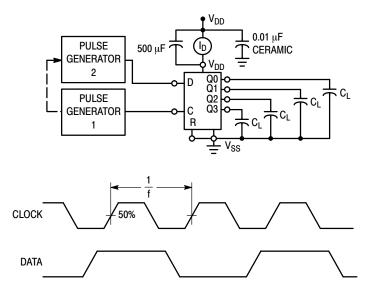


Figure 1. Power Dissipation Test Circuit and Waveform

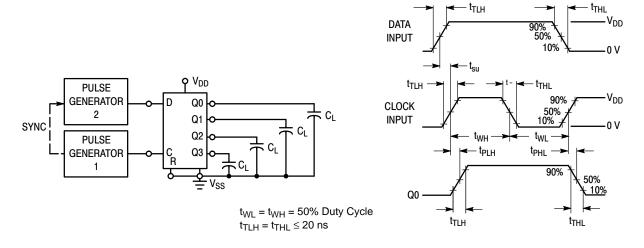


Figure 2. Switching Test Circuit and Waveforms

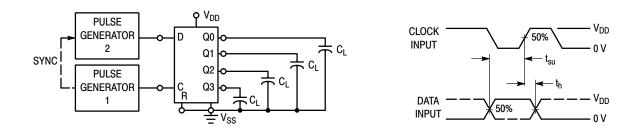
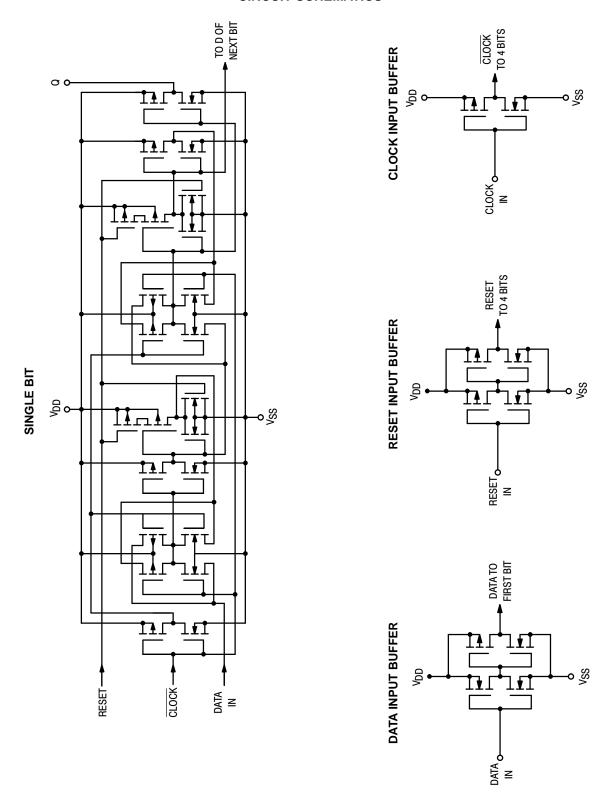


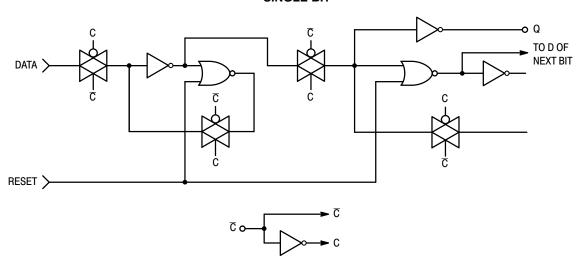
Figure 3. Setup and Hold Time Test Circuit and Waveforms

# **CIRCUIT SCHEMATICS**

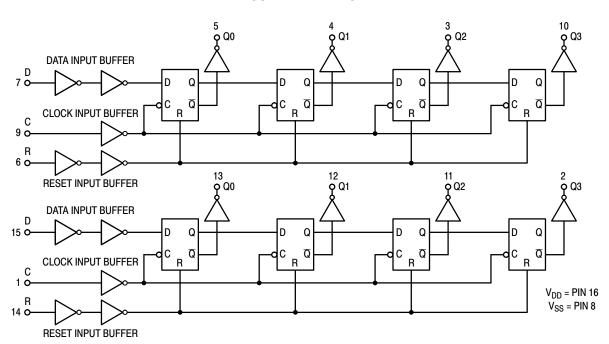


#### **LOGIC DIAGRAMS**

#### **SINGLE BIT**



#### **COMPLETE DEVICE**



# **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	COL DEDING	FOOTPRINT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	3 FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		5.40 <del>→</del>
								7	,.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	T)		. 1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			<b>↓ └──</b> ·	" 🗀
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	•,		<del>-</del> —	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)	16	5X <b>T</b>	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		0.5	iii I	· —
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.0		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPU	T)			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPU	T)			— V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				<u> </u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 + - + -
								<del></del> •	_ <del>-</del> <del> </del> ↑
									DIMENSIONS: MILLIMETERS
									DIMENSIONS: MILLIMETERS

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